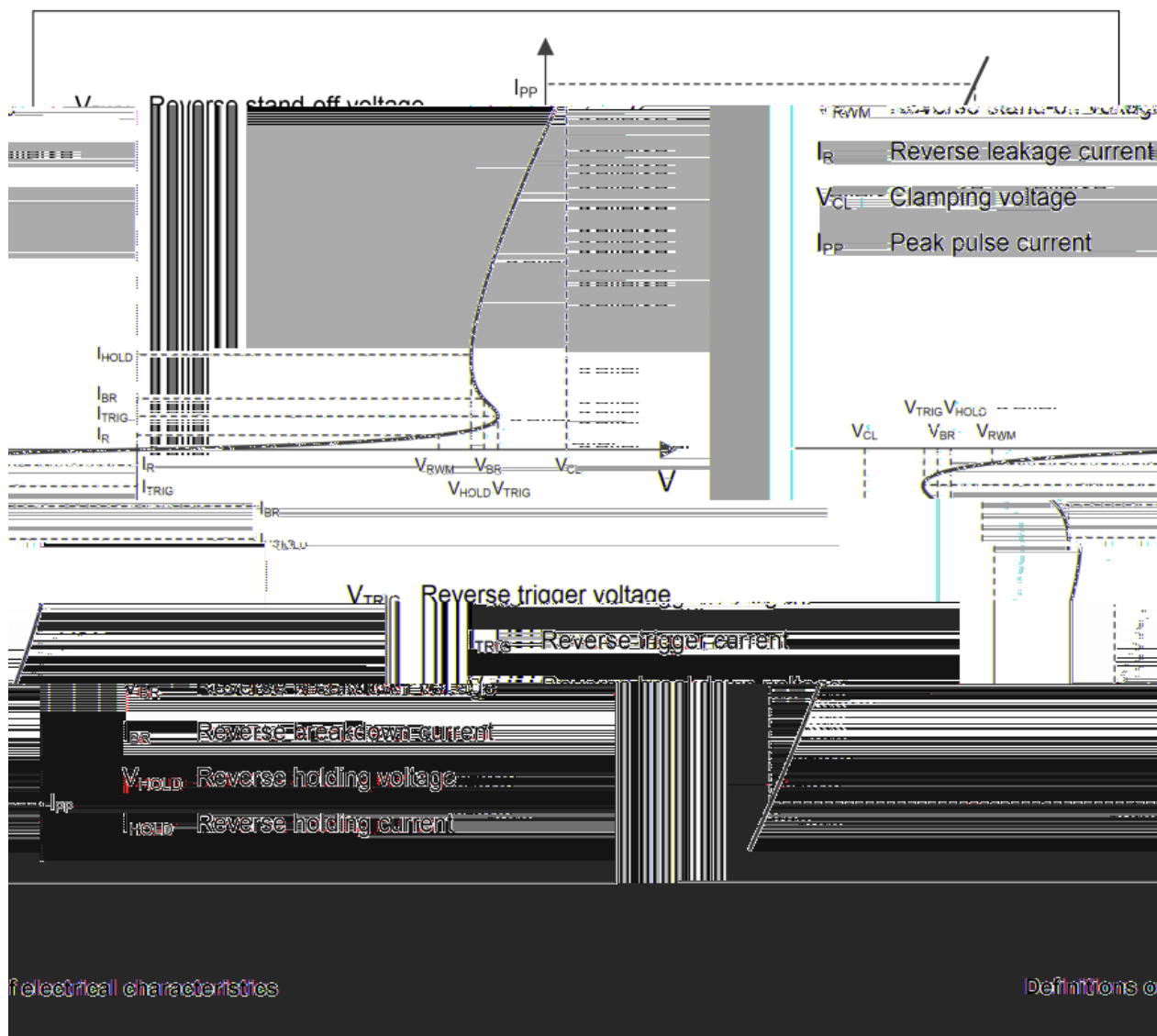


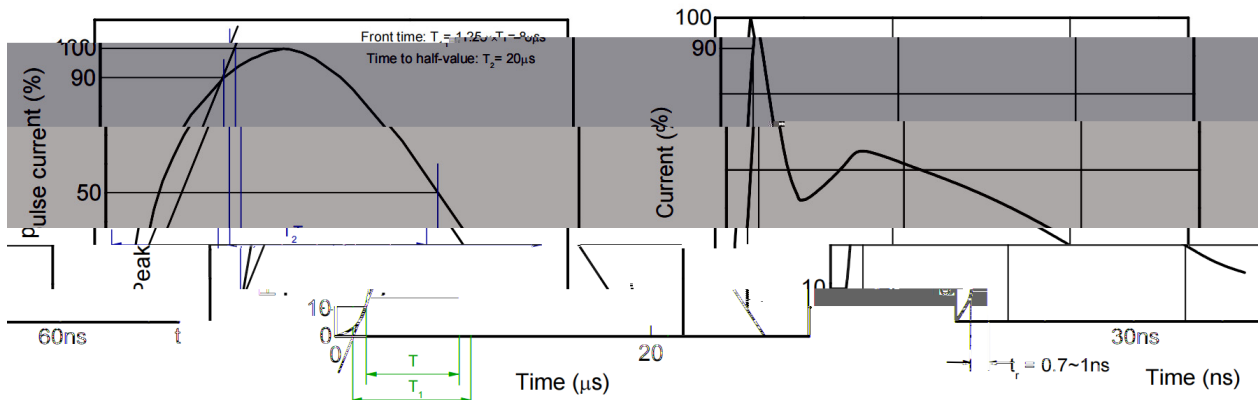
Parameter	Symbol	Rating	Unit
Peak pulse power ($t_p = 8/20\mu s$)	P_K	420	W
Peak pulse current ($t_p = 8/20\mu s$)	I_{PP}	7	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 30	KV
ESD according to IEC61000-4-2 contact discharge		± 30	
Junction temperature	T_J	125	$^{\circ}C$
Storage temperature	T_{STG}	-55~+150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse maximum working voltage	V_{RWM}				± 36	V
Reverse leakage current	I_R	$V_{RWM} = \pm 36V$			100	nA
Reverse breakdown voltage ¹⁾	V_{BR}	$I_T = 1mA$	36			V
Clamping voltage ²⁾	V_C	$I_{PP} = 1A \ t_p = 8/20\mu s$		46	48	V
		$I_{PP} = 7A \ t_p = 8/20\mu s$		75	77	V
		$V_{ESD}=8KV$ ³⁾		65		V
Junction capacitance	C_J	$V_R = 0V \ f = 1MHz$		15	20	pF
Clamping voltage ⁴⁾	V_{CL}	$I_{PP} = 16A \ t_p = 100ns$		60		V
Dynamic resistance ⁴⁾	R_{DYN}			0.22		Ω

Notes:

- 1) V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25 $^{\circ}C$.
- 2) Non-repetitive current pulse, according to IEC61000-4-5.
- 3) Contact discharge mode, according to IEC61000-4-2.
- 4) TLP parameter: $Z_0 = 50\Omega$, $t_p = 100ns$, $t_r = 2ns$, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.

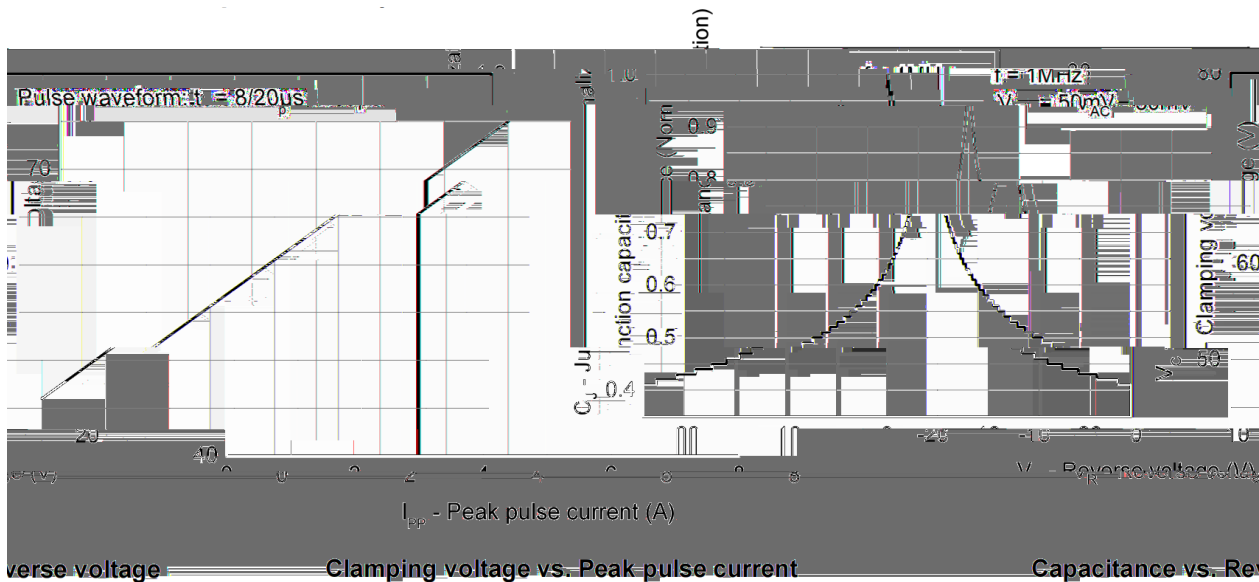




Form per IEC61000-4-2

 8/20 μs waveform per IEC61000-4-5

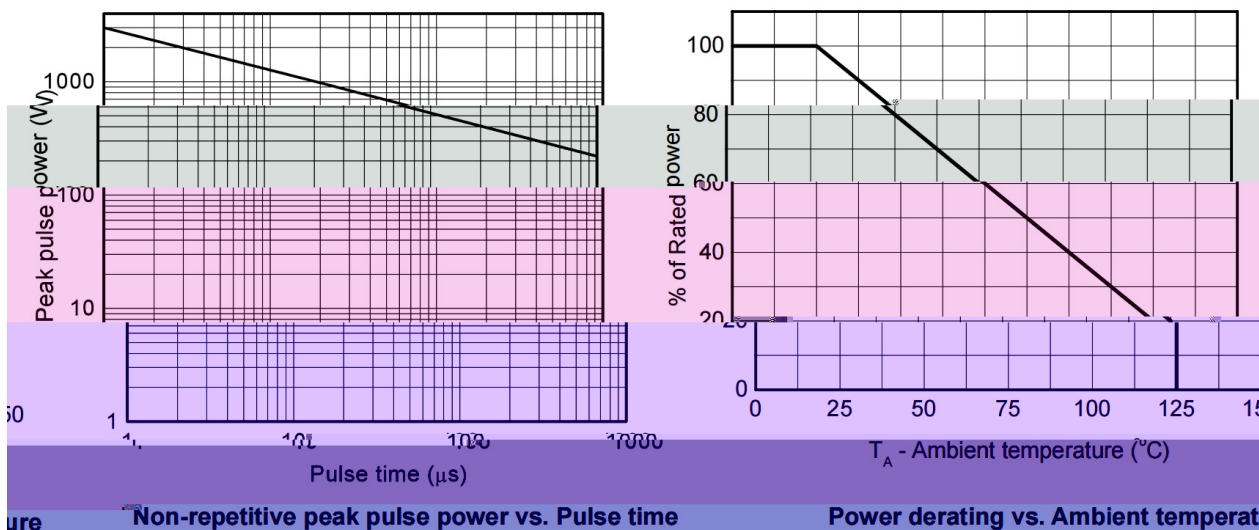
Contact discharge current wavefo



Reverse voltage

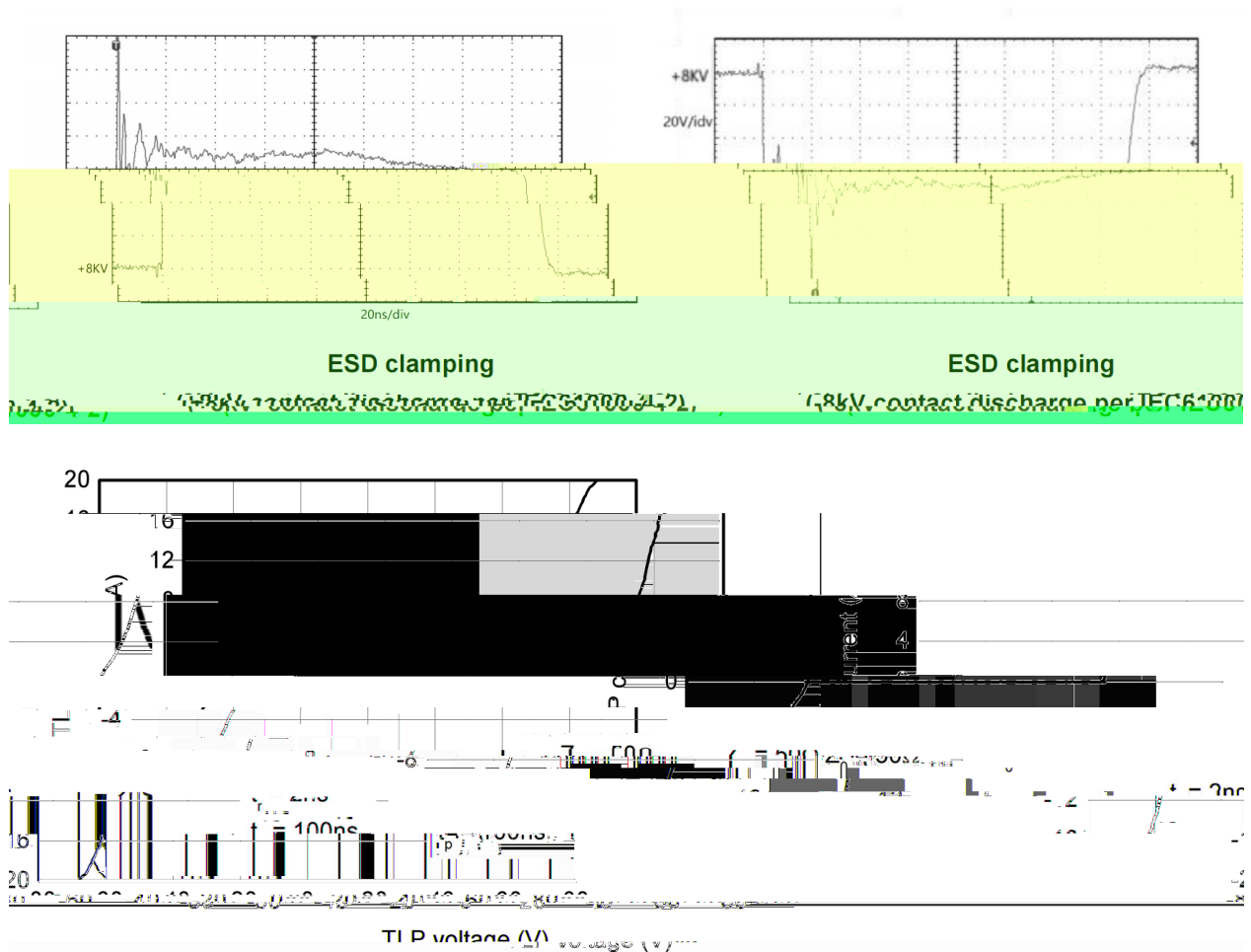
Clamping voltage vs. Peak pulse current

Capacitance vs. Reverse voltage



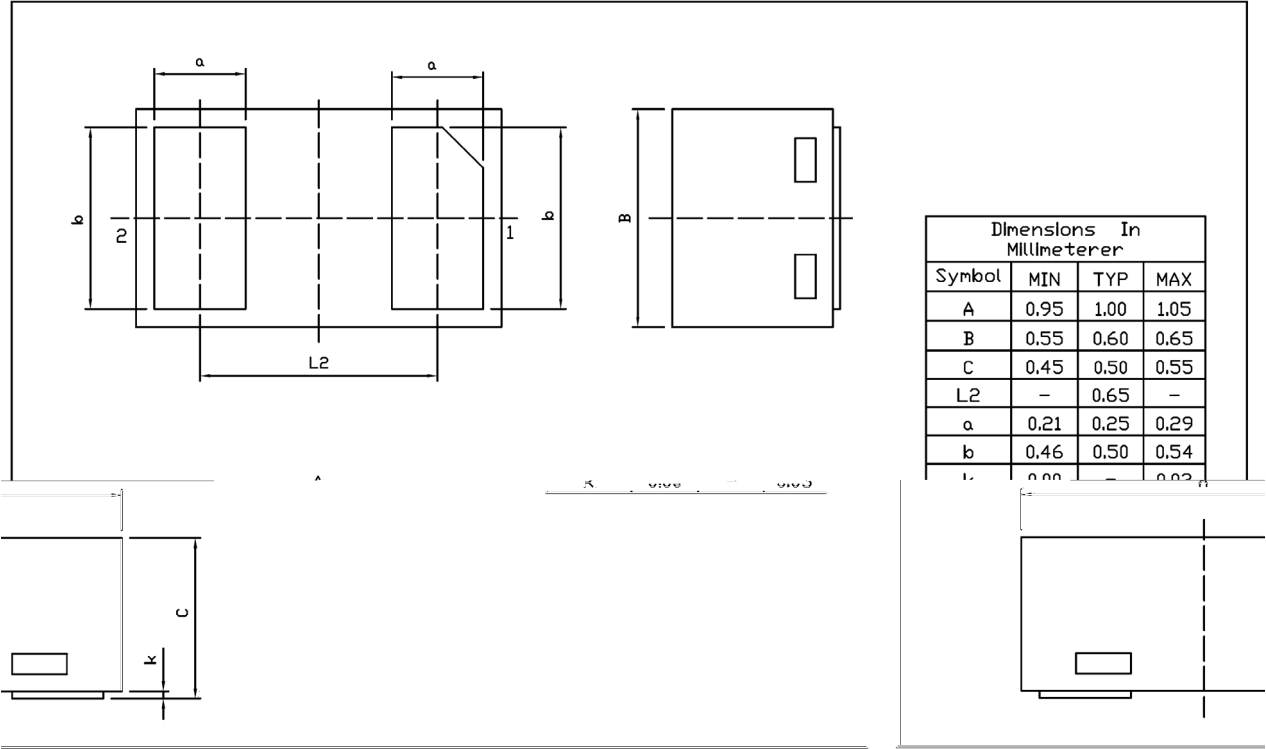
Non-repetitive peak pulse power vs. Pulse time

Power derating vs. Ambient temperature



DFN1006-2L

Unit:mm



Rev.01 202108



Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245 5

5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260 5

10 1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
DFN1006-2L	10,000	10	100,000	6	600,000	7" ×8	180×120×180	390×385×205